

# INSTRUCTIONS FOR

# TRANSMITTER CONTROL BOARDS 19D416660G1-G8

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#### DESCRIPTION

The 19D416660 Transmitter Control Board is provided in eight different groups for performing the different transmit functions in MASTR II® Tone Control Base Stations. The 19D416660G1 or G5 Board is used in single frequency transmit applications. The 19D416660C2 or G6 Board is required for two frequency transmit applications and, along with the 19D429082G1 Transmitter Control Board, in three and four frequency transmit applications. The 19D416660G3 or G7 Board is used in two frequency transmit with Channel Guard monitor applications and, along with the 19D429082G1 Transmit Control Board, in three or four frequency transmit with Channel Guard monitor applications. The 19D416660G4 or G8 Board is used in single frequency transmit with Channel Guard monitor applications.

#### CIRCUIT ANALYSIS

All groups contain the RCVR NOTCH FILTER and the TX NOTCH FILTER for removing the 2175 Hz Secur-it tone from the audio path. The receive audio path is connected from the Audio Board via RCVR NOTCH FILTER OUTPUT lead D14 to the Transmitter Control Board. The filter is composed of series resonant shunts L6-C10 and L4-C7 along with parallel resonant trap C9-L5. The filter notches out the 2175 Hz components from the receiver audio and returns the audio via RX NOTCH OUT lead D13 to the Audio Board.

The 2175 Hz tone is notched from the transmit audio path by the TX NOTCH FILTER, composed of series resonant shunts L7-C11 and L9-C14 together with paral-

lel resonant trap L8-C13. The transmit audio is connected to the filter via LINE AUDIO path A8 and returned to the Audio Board via NOTCHED AUDIO path A9.

## Single Frequency Transmit

In single frequency transmit applications, a function tone frequency of 1950 Hz is applied to the audio pair at the remote control console. This tone is connected to the 19D416660G1 or G5 Transmitter Control Board on the LIMITED AUDIO lead A10. An LC filter, composed of L1-C1 tuned to the 1950 Hz function tone, turns off diode CR1 on the positive peaks and allows Q1 to turn on through R2. Conduction of Q1 applies a low to the input of gate U1-D.

The grounded Secur-it DET lead D7 is connected to inverter U3-C, applying a high to the input of U1-A. The low output of U1-A is connected back to U1-D, latching the flip-flop. The low output of U1-A is also inverted by U1-C and applied to NAND gate U1-B. The inverted high Secur-it DET lead is also connected to the input of U1-B. The resultant output of U1-B is inverted by U3-B and the high turns on Q3. Conduction of Q3 grounds the PTT path to key the station transmitter. The high output of U1-C turns on Q15, grounding the LIMITED AUDIO path in the G1-G4 boards as long as the flip-flop remains latched. In the G5-G8 boards, conduction of Q15 resets the WINDOW ONE SHOT after the transmit function tone is detected. This disables the LIMITED AUDIO path long before voice audio is present. Unkeying the transmitter removes the ground from the DET lead D7, applying a low to pin 2 of Ul-A. This unlatches the flip-flop. Operating the XMIT DISABLE switch S2 to the DISABLE position opens the PTT path and applies

ground to the XMIT DISABLE Indicator LED CR11, turning on the light.

# Two, Three or Four Frequency Transmit

Transmit Control Board 19D416660G2 or G6 is required for two frequency and three or four frequency transmit applications. The 1950 Hz tone frequency detector operates in the same manner as described for the G1 or G5 Board. The PTT path is connected in the same configuration.

When TX F2 tone (1850 Hz) is selected at the remote control console, the tone is detected at the F2 filter (L2-C3), back biasing CR6 and turning on Q6. This latches flip-flop U2-A, U2-D, applying a low to gate U1-C. The transmitter is keyed as previously described. The high output of U2-D turns on Q8 which, in turn, grounds the XMIT F2 lead A2 to select the transmit F2 oscillator and operates Q9. Conduction of Q9 applies a high to TX F2 INTERCONNECT lead D11.

If the TX F1 tone is selected, the high output from U1-D turns on Q4 and Q5, applying high to TX F1 INTERCONNECT lead D10 and applying ground to XMIT F1 lead A5 to select the transmit F1 oscillator.

When TX F2 is selected, the high from the output of U2-D also turns on Q7, applying ground to XMIT F2 Indicator LED CR9 to turn on the light.

In local PTT operation, with no function tone present on the LIMITED AUDIO path, the Secur-it DET lead D7 is high. Grounding the PTT lead D6 with the local PTT microphone turns on Q13 which, in turn, operates Q14 and forward biases CR3. The low input to U2-C is inverted and applied to NAND gate U2-D. The GT DET

lead, which is high, is also connected to NAND gate U2-C. The resulting low output keys the transmitter through F1-F2 service switch S1. The position of S2 determines which transmitter oscillator is keyed in local PTT operation.

#### **Channel Guard Disable**

The Channel Guard Disable function requires the use of Transmitter Control Board 19D416660G4 or G8 in single frequency transmit systems and 19D416660G3 or G7 in two, three and four frequency transmit systems.

The single frequency and two frequency detection circuits function as described for the G1, G2, G5 or G6 boards. The Channel Guard Disable detector circuit (2050 Hz) consists of the filter (L3-C5) which, when it detects the presence of 2050 Hz back biases CR7 and turns on Q10. Flip-flop U3-A, U3-D is latched and turns off Q11. The high at the collector of Q11 turns Q16 on, applying ground to the CG DISABLE lead A7 to disable Channel Guard.

Whenever the station transmitter is keyed, Q13 and Q14 conduct, forward biasing CR4 and unlatching the flip-flop. Q11 is turned on, turning off Q16 and enabling Channel Guard. The CG MON-XMIT DISABLE service switch S2 applies a ground to the input of the flip-flop at U3-D pin 13 when placed in the MON position. This ground operates the disable circuit as described previously.

The high output of U3-D (when Channel Guard disable is selected) will turn on Q12, applying ground to CG MON Indicator LED CR10 and turning on the light.



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#### TRANSMITTER CONTROL BOARD 19D416660G1, G5

C1
C1 19C307114P1302G Polystyrene: 13,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C2 19A116080P110 Polyester: 0.33 μF ±10%, 50 VDCW. C3 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C8 5496267P19 Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D. C9 19C307114P1002G Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C10 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C12 5496267P19 Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D. C13 19C307114P1002G Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C14 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C16 5496267P2 Tantalum: 47 μF ± 20%, 6 VDCW; sim to Sprague Type 150D. C17 19A700233P7 Ceramic: 1000 pF ± 20%, 50 VDCW. C18* 7491827P102 Ceramic: 0.01 μF -30 +80%, 50 VDCW. Ceramic: 0.01 μF -30 +80%, 50 VDCW, sim to Sprague 19C180.  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV. Light Emitting Diode: Red; sim to GE 22L-2. Silicon: Rectifier; sim to 1N4004.
C1 19C307114P1302G Polystyrene: 13,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C2 19A116080P110 Polyester: 0.33 μF ±10%, 50 VDCW. C3 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C8 5496267P19 Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D. C9 19C307114P1002G Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C10 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C12 5496267P19 Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D. C13 19C307114P1002G Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C14 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM. C16 5496267P2 Tantalum: 47 μF ± 20%, 6 VDCW; sim to Sprague Type 150D. C17 19A700233P7 Ceramic: 1000 pF ± 20%, 50 VDCW. C18* 7491827P102 Ceramic: 0.01 μF -30 +80%, 50 VDCW. Ceramic: 0.01 μF -30 +80%, 50 VDCW, sim to Sprague 19C180.  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV. Light Emitting Diode: Red; sim to GE 22L-2. Silicon: Rectifier; sim to 1N4004.
C2 19A116080P110 C7 19C307114P6801G C8 5496267P19
C7 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C8 5496267P19 Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.  C9 19C307114P1002G Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C10 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C12 5496267P19 Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.  C13 19C307114P1002G Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C14 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C15 5496267P2 Tantalum: 47 μF ± 20%, 6 VDCW; sim to Sprague Type 150D.  C17 19A700233P7 Ceramic: 1000 pF ± 20%, 50 VDCW.  C18* 7491827P102 Ceramic: 0.01 μF -30 +80%, 50 VDCW, sim to Sprague 19C180.  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.  Light Emitting Diode: Red; sim to GE 22L-2.  CR12 T324ADP1041 Silicon: Rectifier; sim to 1N4004.  L1 19B205354G6 Coil.  L4 19B205354G5 Coil.  L6 19B205354G5 Coil.  L6 19B205354G4 Coil.
C8 5496267P19 Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.  C9 19C307114P1002G Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C10 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C12 5496267P19 Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.  C13 19C307114P1002G Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C14 19C307114P6801G Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C16 5496267P2 Tantalum: 47 μF ± 20%, 6 VDCW; sim to Sprague Type 150D.  C17 19A700233P7 Ceramic: 1000 pF ± 20%, 50 VDCW.  C18* 7491827P102 Ceramic: 1000 pF ± 20%, 50 VDCW.  Ceramic: 0.01 μF -30 +80%, 50 VDCW, sim to Sprague 19C180.  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.  Light Emitting Diode: Red; sim to GE 22L-2.  Silicon: Rectifier; sim to 1N4004.
C9 19C307114P1002G Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C10 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C12 5496267P19 Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.  C13 19C307114P1002G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C14 19C307114P6801G Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  C16 5496267P2 Tantalum: 47 μF ± 20%, 6 VDCW; sim to Sprague Type 150D.  C17 19A700233P7 Ceramic: 1000 pF ± 20%, 50 VDCW.  C18* 7491827P102 Ceramic: 0.01 μF -30 +80%, 50 VDCW, sim to Sprague 19C180.  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.  Light Emitting Diode: Red; sim to GE 22L-2.  Silicon: Rectifier; sim to 1N4004.  L1 19B205354G6 Coil.  L5 19B205354G5 Coil.  L6 19B205354G5 Coil.  L6 19B205354G4 Coil.
C10 and C11   19C307114P6801G   Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.     C12   5496267P19   Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.     C13   19C307114P1002G   Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.     C14   19C307114P6801G   Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.     C15   5496267P2   Tantalum: 47 μF ± 20%, 6 VDCW; sim to Sprague Type 150D.     C17   19A700233P7   Ceramic: 1000 pF ± 20%, 50 VDCW.     C18*   7491827P102   Ceramic: 0.01 μF -30 +80%, 50 VDCW, sim to Sprague 19C180.     CR11   19A115250P1   Silicon, fast recovery, 225 mA, 50 PIV.     CR11   162B3011P0002   Light Emitting Diode: Red; sim to GE 22L-2.     CR12   T324ADP1041   Silicon: Rectifier; sim to 1N4004.     L1   19B205354G6   Coil.     L5   19B205354G5   Coil.     L6   19B205354G4   Coil.     L8   19B205354G4   Coil.     Coil.     C13   C14
Sprague Type 150D.
temp coef -120+30 PPM.  Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.  Tantalum: 47 μF ± 20%, 6 VDCW; sim to Sprague Type 150D.  C17 19A700233P7 Ceramic: 1000 pF ± 20%, 50 VDCW.  C18* 7491827P102 Ceramic: 0.01 μF -30 +80%, 50 VDCW, sim to Sprague 19C180.  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.  Light Emitting Diode: Red; sim to GE 22L-2.  Silicon: Rectifier; sim to 1N4004.  L1 19B205354G6 Coil.  L4 19B205354G5 Coil.  L5 19B205354G4 Coil.  L6 19B205354G4 Coil.
temp coef -120+30 PPM.  Tantalum: 47 μF ± 20%, 6 VDCW; sim to Sprague Type 150D.  C17 19A700233P7 Ceramic: 1000 pF ± 20%, 50 VDCW.  C18* 7491827P102 Ceramic: 0.01 μF -30 +80%, 50 VDCW, sim to Sprague 19C180.  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.  CR11 162B3011P0002 Light Emitting Diode: Red; sim to GE 22L-2.  Silicon: Rectifier; sim to 1N4004.  L1 19B205354G6 Coil.  L4 19B205354G5 Coil.  L5 19B205354G4 Coil.  L6 and L7 L8 19B205354G4 Coil.
Sprague Type 150D.
C18* 7491827P102 Ceramic: 0.01 µF -30 +80%, 50 VDCW, sim to Sprague 19C180.  CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV.  Light Emitting Diode: Red; sim to GE 22L-2.  Silicon: Rectifier; sim to 1N4004.  L1 19B205354G6 Coil.  L4 19B205354G5 Coil.  L5 19B205354G4 Coil.  L6 and L7  L8 19B205354G4 Coil.
to Sprague 19C180.  CR1
CR1 19A115250P1 Silicon, fast recovery, 225 mA, 50 PIV. Light Emitting Diode: Red; sim to GE 22L-2. Silicon: Rectifier; sim to 1N4004.  L1 19B205354G6 Coil. L4 19B205354G5 Coil. L5 19B205354G4 Coil. L6 and L7 L8 19B205354G4 Coil.
CR11 162B3011P0002 Light Emitting Diode: Red; sim to GE 22L-2.  Silicon: Rectifier; sim to 1N4004.  L1 19B205354G6 Coil. L4 19B205354G4 Coil. L6 19B205354G5 Coil. L6 19B205354G5 Coil. L7 L8 19B205354G4 Coil.
CR12 T324ADP1041 Silicon: Rectifier; sim to 1N4004.  L1 19B205354G6 Coil. L4 19B205354G4 Coil. L5 19B205354G4 Coil. L6 19B205354G5 Coil. L7 L8 19B205354G4 Coil.
L1 19B205354G6 Coil. L4 19B205354G5 Coil. L5 19B205354G4 Coil. L6 19B205354G5 Coil. L7 Coil. L8 19B205354G4 Coil.
L1 19B205354G6 Coil. L4 19B205354G5 Coil. L5 19B205354G4 Coil. L6 19B205354G5 Coil. L7 Coil. L8 19B205354G4 Coil.
L4 19B205354G5 Coil. L5 19B205354G4 Coil. L6 19B205354G5 Coil. L7 Coil. L8 19B205354G4 Coil.
L5 19B205354G4 Coil.  L6 19B205354G5 Coil.  L7 L8 19B205354G4 Coil.
L6 and L7 L8 19B205354G4 Coil.
and L7 L8 19B205354G4 Coil.
L7   L8   19B205354G4   Coil.
L9 19B205354G5 Coil.
1 1
PLUGS
P9 Part of printed wire board.
TRANSISTORS
Q1 19A700023P1 Silicon, NPN: sim to 2N3904.
Q3 19A115300P4 Silicon, NPN.
Q15 19A116774P1 Silicon, NPN; sim to Type 2N5210.
R1 19A700106P103 Composition: 47K ohms ± 5%, 1/4 w.
R2 3R152P913J Composition: 91K ohms ± 5%, 1/4 w.
R3 19A700106P87 Composition: 10K ohms ± 5%, 1/4 w.
R3 19A700106P87 Composition: 10K ohms ± 5%, 1/4 w. R4 19A700106P39 Composition: 100 ohms ± 5%, 1/4 w.
R3 19A700106P87 Composition: 10K ohms ± 5%, 1/4 w. R4 19A700106P39 Composition: 100 ohms ± 5%, 1/4 w. R5 19A700106P87 Composition: 10K ohms ± 5%, 1/4 w.
R3 19A700106P87 Composition: 10K ohms ± 5%, 1/4 w. R4 19A700106P39 Composition: 100 ohms ± 5%, 1/4 w.

<sup>\*</sup>COMPONENTS, ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

SYMBOL	PART NO.	DESCRIPTION
		RESISTORS
R27	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
and R28		
R34	19A700106P67	Composition: 1.5K ohms ± 5%, 1/4 w.
R35	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R36	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
R38	3R152P203J	Composition: 20K ohms ± 5%, 1/4 w.
R40*	3R152P512J	Composition: 5.1K ohms ± 5%, 1/4 w. (Added for tone repeater applications. (Added by Rev. B).
R41*	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
		·····switches ·····
S2	19B209261P17	Slide: 2 PTT, sim. to Switchcraft 46313-TD4.
		TEST POINTS
TP1 thru TP3	19B211379P1	Spring (Test Point).
TP5	19B211379P1	Spring (Test Point).
		·····INTEGRATED CIRCUITS ·····
U1	19A700037P301	Digital: Quad 2-Input NAND gate; sim to 74LS00.
U3	19A700037P301	Digital: Quad 2-Input NAND gate; sim to 74LS00.
		····· MISCELLANEOUS ·····
	19A701332P4	Insulator, washer: nylon. (Used with Q3).
	19B219690G1	Handle assembly.
	19B219702P2	Panel.
	4032480P1	Nut, sheet spring: sim to Vector Electronic Co. No. 440.
	19B201074P204	Tap screw, phillips POZIDRIV: No. 4-40 x 1/4.
	N404P11B6	Lockwasher, internal tooth, No. 4. (Used in G5).
	N80P9003B6	Machine screw, panhead: No. 4-40 x 3/16. (Used in G5).
26	7141225P2	Nut, Hex: 4-40. (Used in G5).

#### PRODUCTION CHANGES

Changes in the equipment to improve perforannee or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A & B - 19D416660G1

Incorporated into initial shipment.

REV. C - Replaced DTL Integrated Circuits U1 and U3 (19A115913P7) with LS-TTL ICs (19A700037P1).

REV. A - 19D416660G5

Replaced DTL Integrated Circuits U1 and U3 (19A115913P7) with LS-TTL ICs (19A700037P1).

REV. B - To increase the reliability of the TX board by providing current limiting on the remote PTT key logic; moved R7 between U3-B Pin 6 and the base of Q3.

# TRANSMITTER CONTROL BOARD 19D416660G2, G6

SYMBOL	PART NO.	DESCRIPTION
		CAPACITORS
C1	19C307114P1302G	Polystyrene: 13,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C2	19A116080P110	Polyester: 0.33 μF ±10%, 50 VDCW.
СЗ	19C307114P1402G	Polystyrene: 14,000 pF ±2%, 100 VDCW, temp_coef -120+30 PPM.
C4	19A116080P110	Polyester: 0.33 μF ±10%, 50 VDCW.
C7	19C307114P6801G	Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C8	5496267P19	Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.
C9	19C307114P1002G	Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C10 and C11	19C307114P6801G	Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C12	5496267P19	Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.
C13	19C307114P1002G	Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C14	19C307114P6801G	Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C16		5496267P2
		Tantalum: 47 μF ± 20%, 6 VDCW; sim to Sprague Type 150D.
C17	19A700233P7	Ceramic: 1000 pF ± 20%, 50 VDCW.
C18	7491827P102	Ceramic: 0.01 $\mu$ F -30 +80%, 50 VDCW, sim to Sprague 19C180.
C19	5496267P17	Tantalum: 1.0 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.
	·	····· DIODES ·····
CR1 thru CR3	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
CR6	19A115250P1	Silicon, fast recovery, 225 mA, 50 PtV.
CR8	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
CR9	162B3011P0002	Light Emitting Diode: Red; sim to GE 22L-2.
CR11	162B3011P0002	Light Emitting Diode: Red; sim to GE 22L-2.
CR12	T324ADP1041	Silicon: Rectifier; sim to 1N4004.
CR13 thru	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
CR17 CR19	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
		inductors
L1 and L2	19B205354G6	Coil.
	19B205354G6	Coil.
L4	19B205354G5	Coil.
L5	19B205354G4	Coil.
L6 and	19B205354G5	Coil.
L7 L8	19B205354G4	Coil.
L9	19B205354G5	Coil.
		PLUGS
P9		Part of printed wire board.
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SYMBOL	PART NO.	DESCRIPTION
		TRANSISTORS
Q1 and	19A700023P1	Silicon, NPN: sim to 2N3904.
Q2		
Q3	19A115300P4	Silicon, NPN.
Q4	19A700023P1	Silicon, NPN: sim to 2N3904.
Q5	19A700022P1	Silicon, PNP: sim to 2N3906.
Q6 thru	19A700023P1	Silicon, NPN: sim to 2N3904.
Q8		
Q9	19A700022P1	Silicon, PNP: sim to 2N3906.
Q13	19A115768P1	Silicon, PNP: sim to 2N3702.
Q14	19A700023P1	Silicon, NPN: sim to 2N3904.
Q15	19A116774P1	Silicon, NPN; sim to Type 2N5210.
Q17	19A700023P1	Silicon, NPN: sim to 2N3904.
		RESISTORS
R1	19A700106P103	Composition: 47K ohms ± 5%, 1/4 w.
R2	3R152P913J	Composition: 91K ohms ± 5%, 1/4 w.
R3	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R4	19A700106P39	Composition: 100 ohms ± 5%, 1/4 w.
R5	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R6	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R7	3R152P511J	Composition: 510 ohms ± 5%, 1/4 w.
R8	3R152P133J	Composition: 13K ohms ±5%, 1/4 w.
R9	3R152P302J	Composition: 3K ohms ± 5%, 1/4 w.
R10	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
R11	19A700106P71	Composition: 2.2K ohms ±5%, 1/4 w.
R12 and R13	19A700106P83	Composition: 6.8K ohms ± 5%, 1/4 w.
R14	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
R15	3R152P433J	Composition: 43K ohms ±5%, 1/4 w.
R16	3R152P913J	Composition: 91K ohms ± 5%, 1/4 w.
R17	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R18	3R152P302J	Composition: 3K ohms ± 5%, 1/4 w.
R19	19A700106P71	Composition: 2.2K ohms ±5%, 1/4 w.
R20	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
R27 and	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R28	1	
R29	3R152P303J	Composition: 30K ohms ± 5%, 1/4 w.
R30	19A700106P111	Composition: 100K ohms ± 5%, 1/4 w.
R31	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R32	19A700106P111	Composition: 100K ohms ± 5%, 1/4 w.
R33	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R34	19A700106P67	Composition: 1.5K ohms ± 5%, 1/4 w.
R35	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R36	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
F138	3R152P203J	Composition: 20K ohms ± 5%, 1/4 w.
R40	3R152512J	Composition: 5.1K ohms ± 5%, 1/4 w. (Added for tone repeater applications. (Added by Rev. B).
R41	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R42	19A700106P71	Composition: 2.2K ohms ±5%, 1/4 w.
R43	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
1		•
1		
1		

<sup>\*</sup>COMPONENTS, ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

SYMBOL	PART NO.	DESCRIPTION
		SWITCHES
S1	19B209261P26	Slide: 2PTT, sim. to Switchcraft 46313LDH.
S2	19B209261P17	Slide: 2 PTT, sim. to Switchcraft 46313-TD4.
		·····TEST POINTS ······
	40004400004	
TP1	19B211379P1	Spring (Test Point).
TP6		
		INTEGRATED CIRCUITS
U1 thru	19A700037P301	Digital: Quad 2-Input NAND gate; sim to 74L S00.
U3		74250.
		•
		MISCELLANEOUS
3	19A701332P4	Insulator, washer: nylon. (Used with Q3).
4	19B219690G1	Handle assembly.
6	198219702P4	Panel
9	4032480P1	Nut, sheet spring: sim to Vector Electronic Co. No. 440.
20	19B201074P204	Tap screw, phillips POZIDRIV: No. 4-40 x 1/4.
24	N404P11B6	Lockwasher, internal tooth, No. 4. (Used in G6).
25	N80P9003B6	Machine screw, panhead: No. 4-40 x 3/16. (Used in G6).
26	7141225P2	Nut, Hex: 4-40. (Used in G6).

#### PRODUCTION CHANGES

Changes in the equipment to improve perforamnce or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A 19D416660G2 Incorporated into initial shipment.
- REV. B To prevent retransmission of function tone by remote/repeat stations. Added C18, R40 and R41.
- REV. C To increase the saturation of Q14. Changed R29.
- REV. D To prevent intermittent erroneous receiver selection. Deleted C15. Added C19, CR15 thru CR18, Q17, R42 and R43.
- REV. E Changed board to facilitate manufacturing.
- REV. F To enable use of board in 4-frequency control systems. Changed S1.
- REV. G Replaced DTL. Integrated Circuits U1-U3 (19A115913P7) with LS-TTL ICs (19A700037P1).
- REV. A 19D416660G6

  Replaced DTL Integrated Circuits U1-U3 (19A115913P7) with LS-TTI ICs (19A700037P1).
- REV. B To increae the reliability of the TX board by providing current limiting on the remote PTT key logic; moved R7 between U3-B Pin 6 and the base of Q3.

#### TRANSMITTER CONTROL BOARD 19D416660G3, G7

	19	9D416660G3, G7
SYMBOL	PART NO.	DESCRIPTION
		CAPACITORS
C1	19C307114P1302G	Polystyrene: 13,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C2	19A116080P110	Polyester: 0.33 μF ±10%, 50 VDCW.
СЗ	19C307114P1402G	Polystyrene: 14,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C4	19A116080P110	Polyester: 0.33 μF ±10%, 50 VDCW.
C5	19C307114P1102G	Polystyrene: 11,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C6	19A116080P110	Polyester: 0.33 μF ±10%, 50 VDCW.
C7	19C307114P6801G	Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C8	5496267P19	Tantalum: 22 $\mu$ F $\pm$ 20%, 35 VDCW; sim to Sprague Type 150D.
C9	19C307114P1002G	Polystyrene: 10,000 pF ±2%, 100 VDCW, temp_coef -120+30 PPM.
C10 and C11	19C307114P6801G	Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C12	5496267P19	Tantalum: 22 $\mu$ F $\pm$ 20%, 35 VDCW; sim to Sprague Type 150D.
C13	19C307114P1002G	Polystyrene: 10,000 pF ±2%, 100 VDCW, temp_coef -120+30 PPM.
C14	19C307114P6801G	Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C16	5496267P2	Tantalum: 47 μF ± 20%, 6 VDCW; sim to Sprague Type 150D.
C17	19A700233P7	Ceramic: 1000 pF ± 20%, 50 VDCW.
C18	7491827P102	Ceramic: 0.01 μF -30 +80%, 50 VDCW, sim to Sprague 19C180.
C19	5496267P17	Tantalum: 1.0 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.
1		DIODES
CR1 thru CR4	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
CR6 thru	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
CR8 CR9 thru CR11	162B3011P0002	Light Emitting Diode: Red; sim to GE 22L-2.
CR12	T324ADP1041	Silicon: Rectifier; sim to 1N4004.
CR13 thru	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
CR17 CR19	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
		······inductors······
L1 thru L3	19B205354G6	Coil.
L4	19B205354G5	Coil.
L5	19B205354G4	Coil.
L6 and L7	19B205354G5	Coil.
L8	19B205354G4	Coil.
لقا ا	19B205354G5	Coil.
		<u> </u>

<sup>\*</sup>COMPONENTS, ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

SYMBOL	PART NO.	DESCRIPTION
		BILICO
<b>D</b> C		Put of a dead of the bound
P9		Part of printed wire board.
		TRANSISTORS
Q1	19A700023P1	Silicon, NPN: sim to 2N3904.
and Q2		
Q3	19A115300P4	Silicon, NPN.
Q4	19A700023P1	Silicon, NPN: sim to 2N3904.
Q5	19A700022P1	Silicon, PNP: sim to 2N3906.
Q6	19A700023P1	Silicon, NPN: sim to 2N3904.
thru Q8		
Q9	19A700022P1	Silicon, PNP: sim to 2N3906.
Q10	19A700023P1	Silicon, NPN: sim to 2N3904.
thru Q12		
	19A115768P1	Silicon, PNP: sim to 2N3702.
Q13 Q14	19A115768P1 19A700023P1	Silicon, PNP: sim to 2N3904.
Q14 Q15	19A700023P1 19A116774P1	Silicon, NPN; sim to ZN3904. Silicon, NPN; sim to Type 2N5210.
Q16	19A700023P1	Silicon, NPN: sim to 1ype 2N3210.
and	.57.7000201	Sanding the transfer and the sand to
Q17		
		RESISTORS
<b>B1</b>	19A700106P103	Composition: 47K ohms ± 5%, 1/4 w.
R2	3R152P913J	Composition: 91K ohms ± 5%, 1/4 w.
R3	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R4	19A700106P39	Composition: 100 ohms ± 5%, 1/4 w.
R5	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R6	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R7	3R152P511J	Composition: 510 ohms ± 5%, 1/4 w.
R8	3R152P133J	Composition: 13K ohms ±5%, 1/4 w.
R9	3R152P302J	Composition: 3K ohms ± 5%, 1/4 w.
R10	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
R11	19A700106P71	Composition: 2.2K ohms ±5%, 1/4 w.
R12	19A700106P83	Composition: 6.8K ohms ± 5%, 1/4 w.
and R13		
R14	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
R15	3R152P433J	Composition: 43K ohms ±5%, 1/4 w.
R16	3R152P913J	Composition: 91K ohms ± 5%, 1/4 w.
R17	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R18	3R152P302J	Composition: 3K ohms ± 5%, 1/4 w.
R19	19A700106P71	Composition: 2.2K ohms ±5%, 1/4 w.
R20	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
R21	3R152P513J	Composition: 5lK ohms ± 5%, 1/4 w. (Used in G3).
R22	3R152P913J	Composition: 91K ohms ± 5%, 1/4 w.
R23	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R24	3R152P133J	Composition: 13K ohms ±5%, 1/4 w.
and	1	
R25	104700106060	Companies 1K short 150/ 4/4
R26	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
R27 and	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R28		1
R29	3R152P303J	Composition: 30K ohms ± 5%, 1/4 w.
R30	19A700106P111	Composition: 100K ohms ± 5%, 1/4 w.
R31	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R32	19A700106P111	Composition: 100K ohms ± 5%, 1/4 w.

SYMBOL	PART NO.	DESCRIPTION
R33	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R34	19A700106P67	Composition: 1.5K ohms ± 5%, 1/4 w.
R35	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R36	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
R37 thru R39	3R152P203J	Composition: 20K ohms $\pm$ 5%, 1/4 w.
R40		Composition: 5.1K ohms ± 5%, 1/4 w. (Added for tone repeater applications. (Added by Rev. B).
R41	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R42	19A700106P71	Composition: 2.2K ohms ±5%, 1/4 w.
R43	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R44	3R152P623J	Composition: 62K ohms $\pm$ 5%, 1/4 w. (Used in G7).
		SWITCHES
S1	19B209261P26	Slide: 2PTT, sim. to Switchcraft 46313LDH.
S2	19B209261P17	Slide: 2 PTT, sim. to Switchcraft 46313-TD4.
		·····TEST POINTS·····
TP1 thru TP7	19B211379P1	Spring (Test Point).
		INTEGRATED CIRCUITS
U1 thru U3	19A700037P301	Digital: Quad 2-Input NAND gate; sim to 74LS00.
	19A701332P4	Insulator, washer: nylon. (Used with Q3).
	19B219690G1	Handle assembly.
6	19B219702P4	Panel.
	4032480P1	Nut, sheet spring: sim to Vector Electronic Co. No. 440.
	19B201074P204	Tap screw, phillips POZIDRIV: No. 4-40 x 1/4.
	N404P11B6	Lockwasher, internal tooth, No. 4. (Used in G7).
	7141225P2	Nut, Hex: 4-40. (Used in G7).

#### PRODUCTION CHANGES

Changes in the equipment to Improve perforamnce or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A 19D416660G3 Incorporated into initial shipment.
- REV. B To prevent retransmission of function tone by remote/repeat stations. Added C18, R40 and R41.
- REV. C To increase the saturation of Q14. Changed R29.
- REV. D To prevent intermittent erroneous receiver selection. Deleted C15. Added C19, CR15 thru CR18, Q17, R42 and R43.
- REV. E Board changed to accommodate EACOM Control Board..
- REV. F Changed board to facilitate manufacturing.
- REV. G To enable use of board in 4-frequency control systems. Changed S1.
- REV. H Replaced DTL Integrated Circuits U1 thru U3 (19A115913P7) with LS-TTL ICs (19A700037P1).
- REV. A 19D416660G7

  To stop the transmitter F1 function from falsing the Channel Guard Disable function. Deleted R21 and added R44.
- REV. B Replaced DTL Integrated Circuits U1 thru U3 (19A115913P7) with LS-TTL, ICs (19A700037P1).
- REV. C To increase the reliability of the TX board by providing current limiting on the remote PTT key logic; moved R7 between U3-8 Pin 6 and the base ob Q3.

# TRANSMITTER CONTROL BOARD 19D416660G4, G8

SYMBOL	PART NO.	DESCRIPTION
1		·····CAPACITORS ·····
C1	19C307114P1302G	Polystyrene: 13,000 pF ±2%, 100 VDCW,
C2	19A116080P110	temp coef -120+30 PPM. Polyester: 0.33 μF ±10%, 50 VDCW.
C5	19C307114P1102G	Polystyrene: 11,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C6	19A116080P110	Polyester: 0.33 µF ±10%, 50 VDCW.
C7	19C307114P6801G	Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C8	5496267P19	Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.
C9	19C307114P1002G	Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C10 and C11	19C307114P6801G	Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C12	5496267P19	Tantalum: 22 μF ± 20%, 35 VDCW; sim to Sprague Type 150D.
C13	19C307114P1002G	Polystyrene: 10,000 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C14	19C307114P6801G	Polystyrene: 6800 pF ±2%, 100 VDCW, temp coef -120+30 PPM.
C16	5496267P2	Tantalum: 47 μF ± 20%, 6 VDCW; sim to Sprague Type 150D.
C17	19A700233P7	Ceramic: 1000 pF ± 20%, 50 VDCW.
C18	7491827P102	Ceramic: 0.01 µF -30 +80%, 50 VDCW, sim to Sprague 19C180.
		DIODES
CR1	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
CR4	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
CR7	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
CR10 and CR11	162B3011P0002	Light Emitting Diode: Red; sim to GE 22L-2.
CR12	T324ADP1041	Silicon: Rectifier; sim to 1N4004.
CR13 and CR14	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
"""		
		······INDUCTORS·····
L1	19B205354G6	Coil.
L3	19B205354G6	Coil.
L4	19B205354G5	Coil.
L5	19B205354G4	Coil.
L6 and L7	19B205354G5	Coil.
LB	19B205354G4	Coil.
L9	19B205354G5	Coil.
		PLUGS
P9		Part of printed wire board.
		TRANSISTORS
Q1 .	19A700023P1	Silicon, NPN: sim to 2N3904.
and		,
C2 C3	19A115300P4	Silicon, NPN.
L		

SYMBOL	PART NO.	DESCRIPTION
Q10 thru Q12	19A700023P1	Silicon, NPN: sim to 2N3904.
Q13	19A115768P1	Silicon, PNP: sim to 2N3702.
Q14	19A700023P1	Silicon, NPN: sim to 2N3904.
Q15	19A116774P1	Silicon, NPN; sim to Type 2N5210.
Q16	19A700023P1	Silicon, NPN: sim to 2N3904.
		·····RESISTORS······
R1	19A700106P103	Composition: 47K ohms ± 5%, 1/4 w.
R2	3R152P913J	Composition: 91K ohms ± 5%, 1/4 w.
R3	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R4	19A700106P39	Composition: 100 ohms ± 5%, 1/4 w.
R5	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R6	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R7	3R152P511J	Composition: 510 ohms ± 5%, 1/4 w.
R21	3R152P513J	Composition: 5lK ohms ± 5%, 1/4 w. (Used in G4 and G4).
R22	3R152P913J	Composition: 91K ohms ± 5%, 1/4 w.
R23	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R24 and R25	3R152P133J	Composition: 13K ohms ±5%, 1/4 w.
R26	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
R27 and R28	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R29	3R152P303J	Composition: 30K ohms ± 5%, 1/4 w.
R30	19A700106P111	Composition: 100K ohms ± 5%, 1/4 w.
R31	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R32	19A700106P111	Composition: 100K ohms ± 5%, 1/4 w.
R33	19A700106P87	Composition: 10K ohms ± 5%, 1/4 w.
R34	19A700106P67	Composition: 1.5K ohms ± 5%, 1/4 w.
R35	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R36	19A700106P63	Composition: 1K ohms ± 5%, 1/4 w.
R37 thru R39	3R152P203J	Composition: 20K ohms ± 5%, 1/4 w.
R40	3R152P512J	Composition: 5.1K ohms ± 5%, 1/4 w. (Added for tone repeater applications. (Added by Rev. B).
R41	3R152P202J	Composition: 2K ohms ± 5%, 1/4 w.
R44	3R152P623J	Composition: 62K ohms $\pm$ 5%, 1/4 w. (Used in G8 and G8).
		·····SWITCHES ·····
S2	19B209261P17	Slide: 2 PTT, sim. to Switchcraft 46313-TD4.
		TEST POINTS
TP1 thru TP3	19B211379P1	Spring (Test Point).
TP5	19B211379P1	Spring (Test Point).
TP7	19B211379P1	Spring (Test Point).
	.522, 10707 1	
U1	19A700037P301	INTEGRATED CIRCUITS Digital: Quad 2-Input NAND gate; sim to
U3	19A700037P301	74LS00. Digital: Quad 2-Input NAND gate; sim to
		74LS00.

\*COMPONENTS, ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

SYMBOL	PART NO.	DESCRIPTION
		····· MISCELLANEOUS ·····
3	19A701332P4	Insulator, washer: nylon. (Used with Q3).
4	19B219690G1	Handle assembly.
5	19B219702P2	Panel.
9	4032480P1	Nut, sheet spring: sim to Vector Electronic Co. No. 440.
20	19B201074P204	Tap screw, phillips POZIDRIV: No. 4-40 x 1/4.
24	N404P11B6	Lockwasher, internal tooth, No. 4. (Used in G4 and G8).
25	N80P9003B6	Machine screw, panhead: No. 4-40 x 3/16. (Used in G4 and G8).
26	7141225P2	Nut, Hex: 4-40. (Used in G4 and G8).

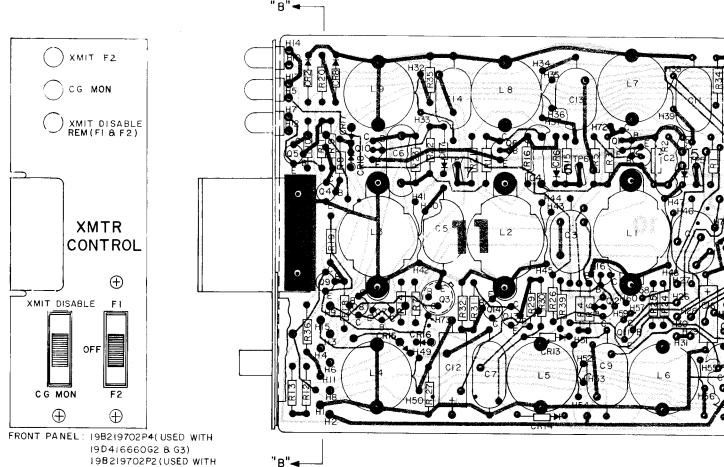
#### PRODUCTION CHANGES

Changes in the equipment to improve perforamnce or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A -19D416660G4 Incorporated into initial shipment.
- REV. B To prevent retransmission of function tone by remote/repeat stations. Added C18, R40 and R41.
- REV. C To increase the saturation of Q14. Changed R29.
- REV. D Board changed to accommodate to EACOM Control Board.
- REV. E Changed board to facilitate manufacturing.
- REV. F Replaced DTL Integrated Circuits U1 and U3 (19A115913P7) with LS-TTL ICs (19A700037P1).
- REV. A <u>19D416660G6</u>

  To stop the transmitter F1 function from falsing the Channel Guard Disable function. Deleted R21 and added R44.
- REV. B Replaced DTL Integrated Circuits U1 and U3 (19A115913P7) with LS-TTL ICs (19A700037PI).
- REV. C To increase the reliability of the TX board by providing current limiting on the remote PTT key logic; moved R7 between U3-8 Pin 6 and the base of C3

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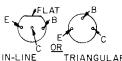


19B219702P2(USED WITH

19D416660G18 G41

HANDLE: 19B219690G1

FRONT PANEL SUPPLIED WITHOUT ELECTRICAL COMPONENTS OR LABELS LEAD IDENTIFICATION FOR QI3

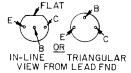


IN-LINE TRIANGULAR VIEW FROM LEAD END

MTG FOR C19

NOTE: LEAD ARRANGEMENT, AND NOT CASE SHAPE IS DETERMINING FACTOR FOR LEAD IDENTIFICATION.

LEAD IDENTIFICATION FOR QI-Q6, Q8-Q10, Q15-Q17



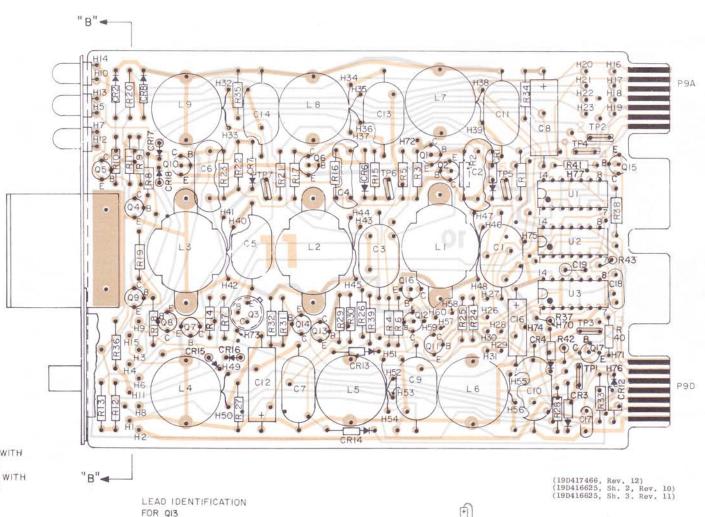
LEAD IDENTIFICATION FOR CR9-CRII



NOTCH OR FLAT IN FLANGE TO DENOTE CATHODE (NEG.) LEAD.

8 9 10 11 12 13 14 7654321 SOLDER SIDE

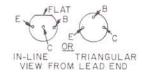
TYP NUMBERING OF CONT. **FINGERS** 



USED WITH 8 G3) (USED WITH 8 641

HOUT LABELS

FOR QI3



NOTE: LEAD ARRANGEMENT, AND NOT CASE SHAPE IS DETERMINING FACTOR FOR LEAD IDENTIFICATION.

LEAD IDENTIFICATION FOR QI-Q6, Q8-Q10, Q15-Q17

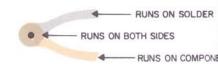
LEAD IDENTIFICATION FOR CR9-CRII

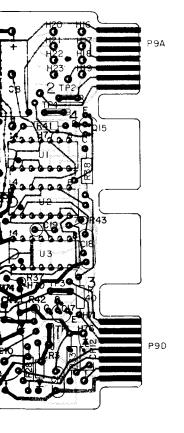


NOTCH OR FLAT IN FLANGE TO DENOTE CATHODE (NEG.) LEAD.

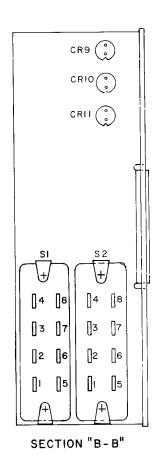
MTG FOR

C19

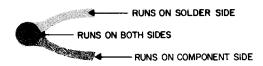




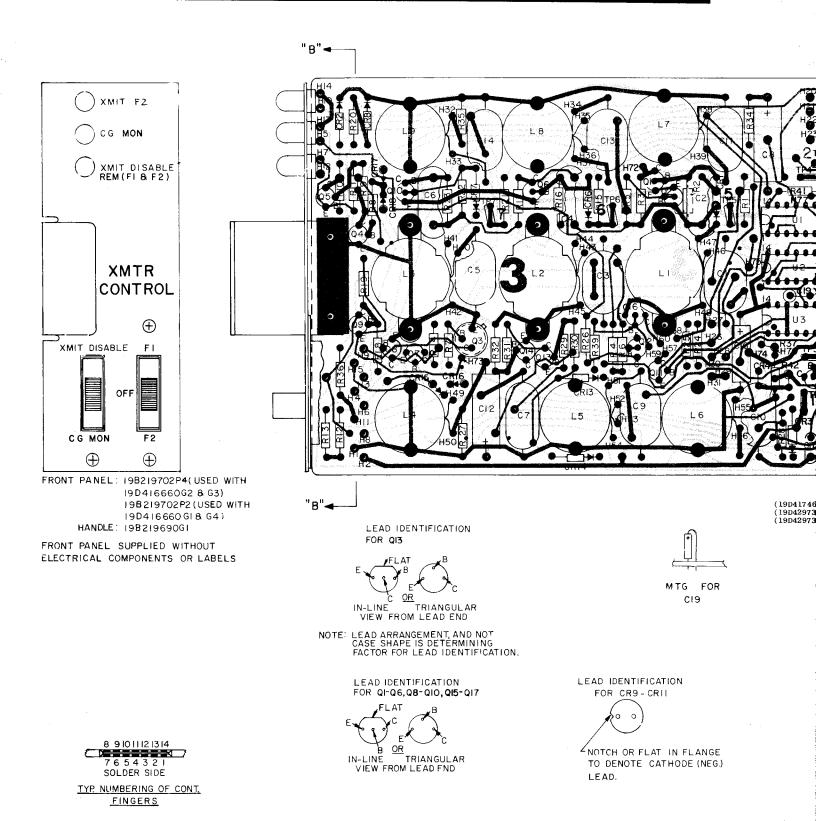




REFER TO WIRING DIAGRAM FOR THE FOLLOWING CONNECT!ONS:							
FROM	то	GP.I	GP. 2	GP. 3	GP. 4		
h17	H21		X	Х			
н19	н23		X	X			
H26	H27			X	X		
Н58	H60			X	X		
H30	H3 I			X	X		
LT-Y	H46	Х	X	X	X		
LI-GY OR R	H47	X	Χ	X	X		
LI-BK	H48	Χ	Χ	Χ	Χ		
L2-Y	H43		Х	Χ	ļ		
L2-GY OR R	H44		Χ	X	<del> </del>		
L2-BK	H45		X	X	<del> </del>		
L3-Y	H40			_ X	X		
L3-GY OR R	H41			- ŷ	X		
L3-BK	H42			X			
L4-BK	H49	X _	, X	X	X		
L4-Y	H50				1 x		
L5-BK L5-NO COLOR	H51 H52	X	X	X	12		
L5-GY OR R	H53	X	X	×	X		
L5-GY OR H	H54	x -	x	- <del>^</del>	<del>  x</del>		
L6-BK	H55	X	X	X	X		
L6-PK	H56	x	<del>  x</del>	X	† <del>x</del>		
L7-Y	H38	X	X	X	X		
L7-BK	H39	x	X	X	X		
L8-Y	H34	X	X	X	X		
L8-GY OR R	H35	x	X	3	X		
L8-NO COLOR	H36	x	X	X	X		
L8-BK	H37	X	X	X	X		
L9-Y	H32	X	X	X	X		
L9-BK	H33	Х	X	X	X		
CR9-ANCDE	H14	<b></b>	X	X	1		
CR9-CATHODE	HIO		X	Х			
CRIO-ANODE	HI3			Х	X		
CRIO-CATHODE	H5	1		Х	Χ		
CRII-ANODE	H7	Х	X	X	X		
CRII-CATHODE	HI2	Х	Х	X	Χ		
SI - <b>4</b>	H3		X	Х			
S1-2	H8		Х	X			
Š1-1	H6		X	X			
S2-I	H4	ļ		X	X		
S2-2	S2-3	1	1	Χ	x		
S2-3	HI5	X	X	X	X		
S2-4	HII	X	X	X	X		
S2-5	S2-7	X	X	X	X		
<b>\$2-5</b>	H9	X	X	X	X		
S2-6	H2	X	X	<u> </u>	X		
H57	H59			X	X		
S1-2	S1-3		X	X			
H77	H76	GP5	GP6	GP7	GP8		

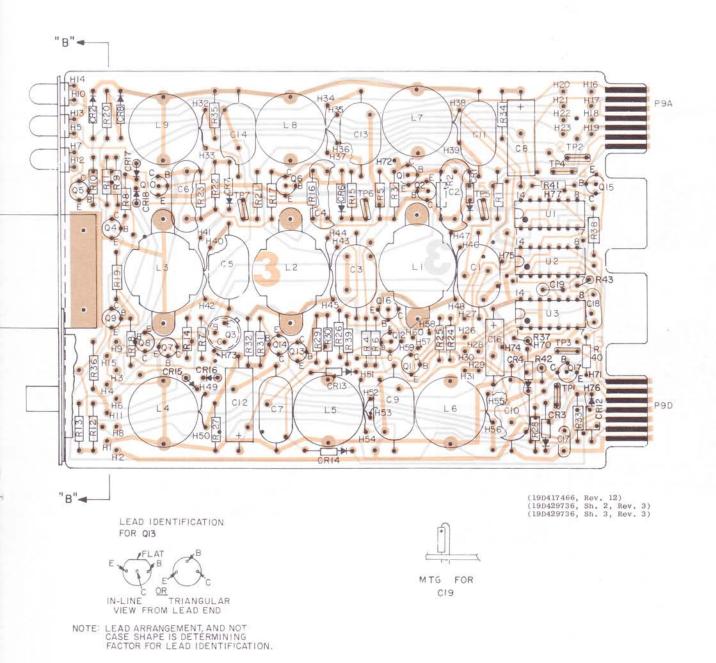


# TRANSMITTER CONTROL BOARDS 19D416660G1-G4



# TRANSMITTER CONTROL BOARDS

19D416660G5-G8



FOR CR9-CRII

100

TO DENOTE CATHODE (NEG.)
LEAD.

RUNS ON BOTH SIDES

RUNS ON COM

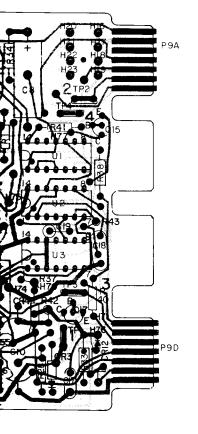
3

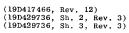
2

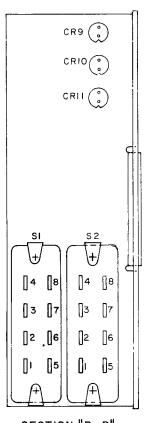
#### **BOARDS**

LEAD IDENTIFICATION FOR QI-Q6,Q8-Q10,Q15-Q17

B OR
IN-LINE TRIANGULAR
VIEW FROM LEAD FND

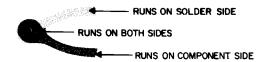


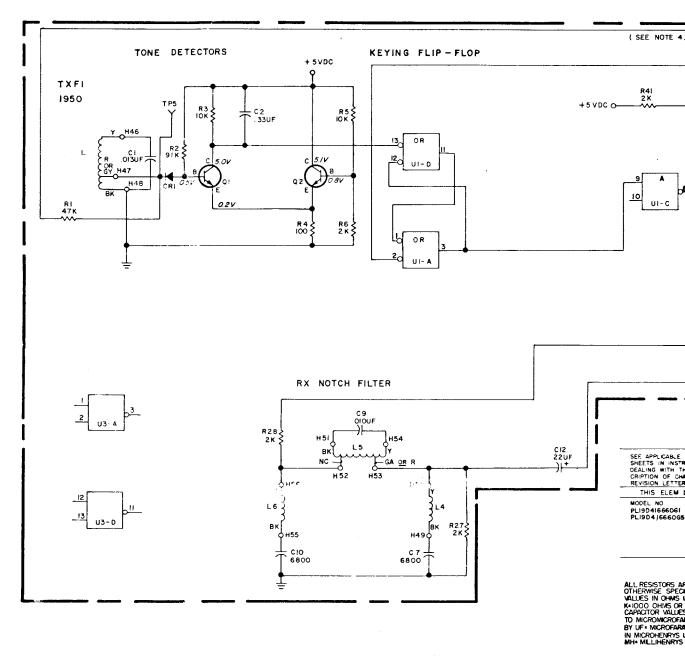




SECTION "B-B"

REFER TO WIRING DIAGRAM FOR							
	THE FOL	LOWING	CONNECTIO	ONS:			
FROM	то	GP.I	GP. 2	GP. 3	GP. 4		
h17	H21	*** · · · · · · · · · · · · · · · · · ·	Х	Х			
н19	H23		X	X	†		
H26	H27			X	X		
H58	H60			X	X		
H30	H31			X	X		
LI-Y	H46	X	Х	Х	X		
LI-GY OR R	H47	X	X	Х	X		
L1-BK	H48	Χ	X	Х	Х		
L2-Y	H43		Х	Х			
L2-GY OR R	H44		X	X			
L2-BK	H45		Х	_ X			
_L3-Y	H40		İ	_ X	X		
L3-GY OR R	H41		ļ	X	У		
L3-BK	H42	-	ļ	X	X		
L4-BK	H49	X	X	X	X		
L4-Y	H50	X	X	X	X		
L5-BK	H51	X	Χ.	X	X		
L5-NO COLOR	H52	X	Х	Х	λ		
L5-GY OR R L5-Y	H53	X	X	X	<u> </u>		
	H54	X	X	X	X		
L6-BK L6-Y	H55	X	X X	X	X		
	H56	X	X	X	X		
L7-Y L7-BK	H38 H39	X	X	X	X		
			<del> </del>				
L8-Y	H34	X	X	X	X		
L8-GY OR R	H35	X	<u>X</u>		X		
L8-NO COLOR	H36	X	X	X	X		
L8-BK L9-Y	H37	X	- <u>^</u>	- X	<del>  X</del>		
	H32		! X	X	X		
L9-BK CR9-ANCDE	H33	X	X	X	X		
				X			
CR9-CATHODE CRIO-ANODE	H!0 HI3	+	X ~	X	X		
CRIO-CATHODE	H5	•	i		<del></del>		
CRIII-ANODE	H7	X	X	X	X		
CRIT-CATHODE	H12	X	Х	X X			
SI-4	H3		X	X	X		
\$1-2	H3		X	×	<del> </del>		
SI-I	H6		- x	- x	+		
S2-1	H4	†	<del></del>	X	×		
S2-2	S2-3	<del> </del>					
S2-3	HI5	X	X	X	X		
\$2-4	HII	X	x	X.	<del>x</del>		
\$2-5	S2-7	x	x	X	x		
\$2-5	Н9	X	X	X	+ ^		
S2-6	H2	×	X	×			
H57	H59	<u> </u>		×	X		
S1-2	SI-3	<del> </del>	+ x	X	<del>  ^ </del>		
H77		CDE			000		
<u> </u>	H76	GP5	GP6	GP7	<u> GP8 _</u>		



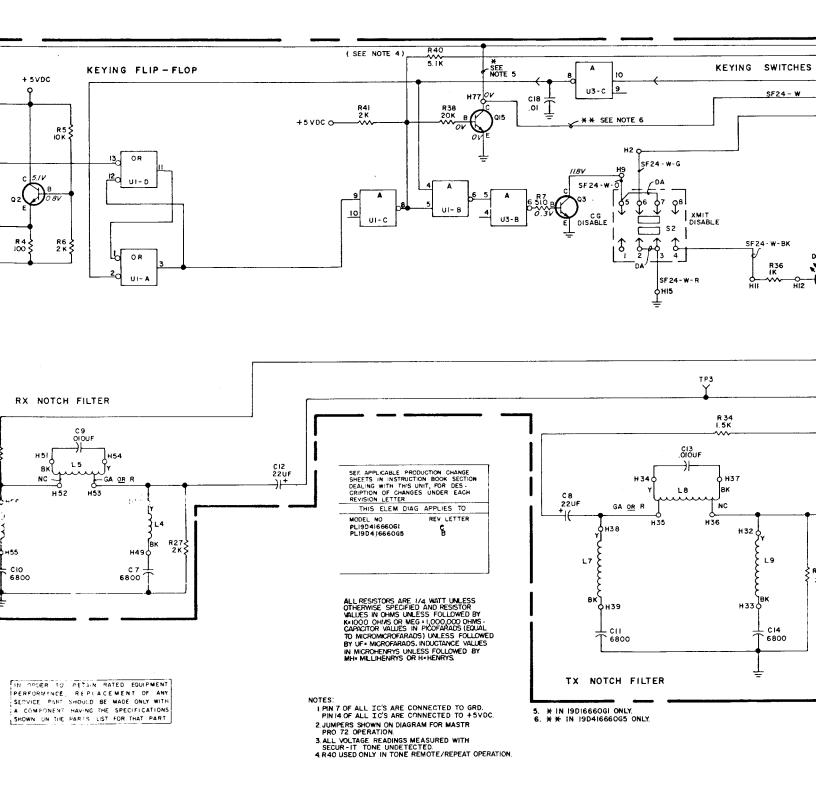


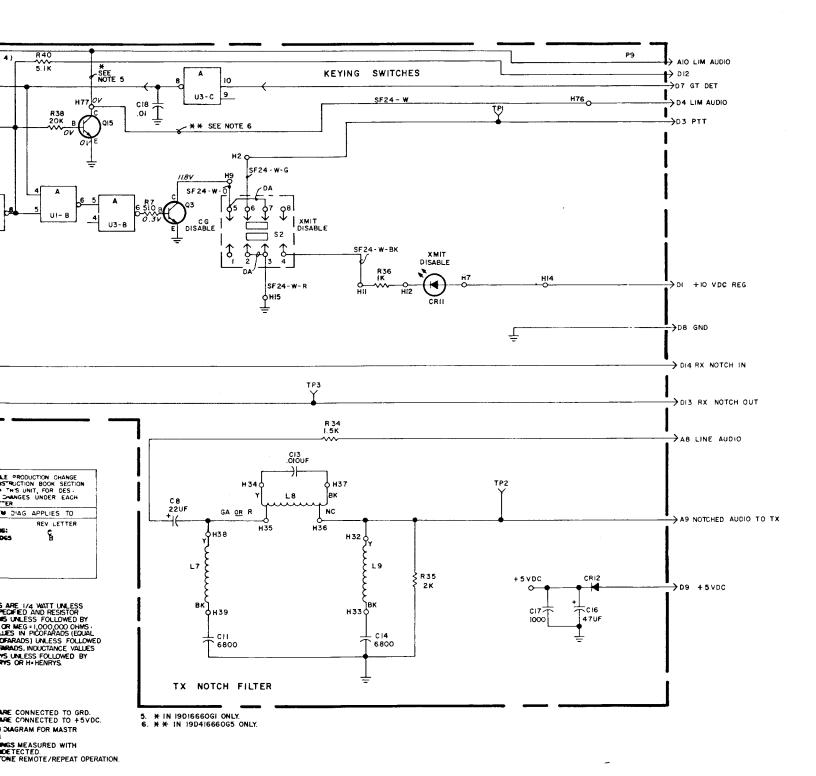
THE OPPORT TO RETAIN MATED EQUIPMENT PERFORMANCE REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART

NOTES:

I.PIN 7 OF ALL IC'S ARE PIN 14 OF ALL IC'S ARE 2. JUMPERS SHOWN ON DU PRO 72 OPERATION.

3. ALL VOLTAGE READING SECUR-IT TONE UNDE:
4.R40 USED ONLY IN TONI

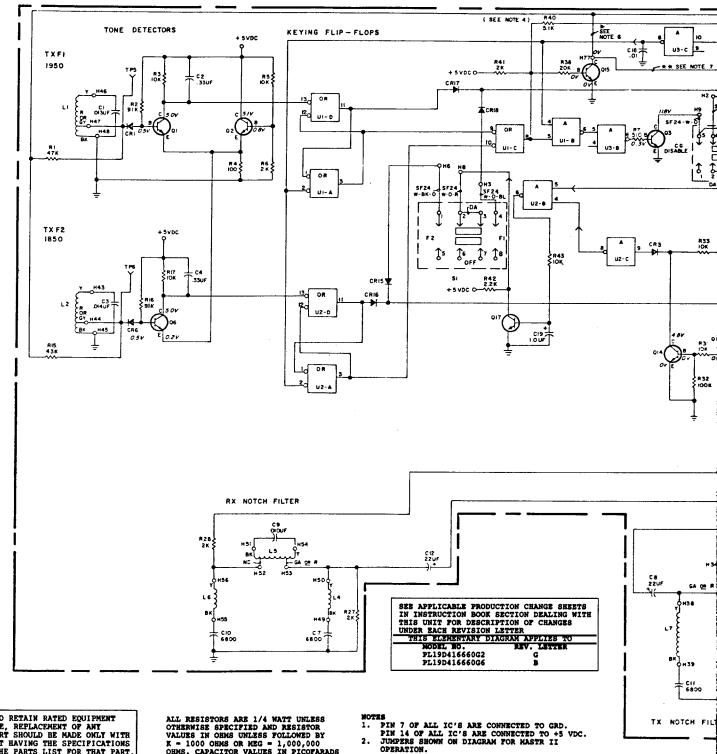




#### TRANSMITTER CONTROL BOARDS

19D416660G1 & G5

(19R621870, Rev. 8)



IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

ALL RESISTORS ARE 1/4 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K = 1000 OHMS OR MEG = 1,000,000 OHMS. CAPACITOR VALUES IN PICOFARADS (EQUAL TO MICROMICROFARADS) UNLESS TO HICKORICKOFARADS, UNLESS FOLLOWED BY ME - MICROFARADS, IN-DUCTANCE VALUES IN MICROHENRYS UN-LESS FOLLOWED BY MH - MILLIHENRYS

- OPERATION.

  ALL VOLTAGE READINGS MEASURED WITH SECUR-IT TONE UNDETECTED.

  4. R40 USED ONLY IN TONE REMOTE/REPEAT OPERATION.

  5. CR14 USED ONLY IN MASTR II OPERATION.

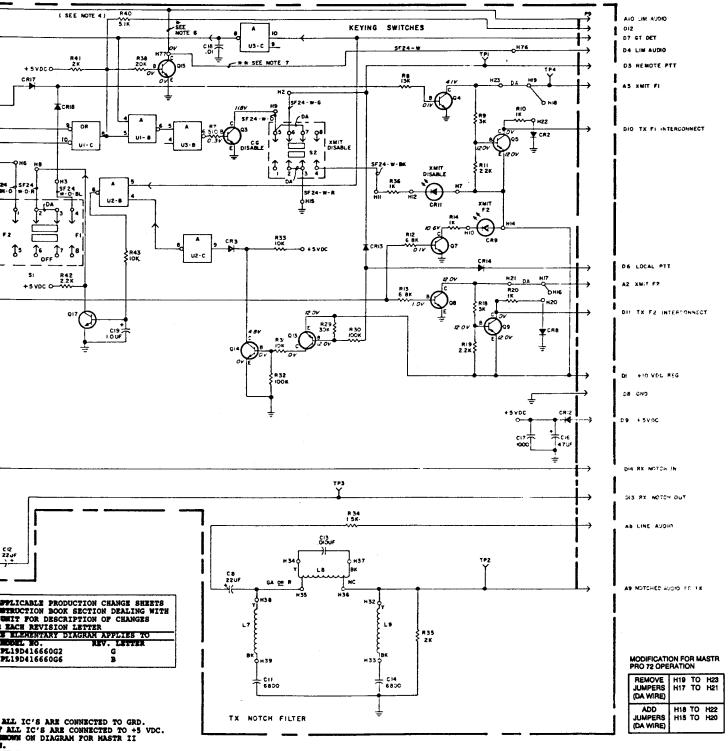
  6. \* IN 19D416660G2 ONLY.

  7. \*\* IN 19D416660G6 ONLY.

### TRANSMITTER CONTROL BOARDS

19D416660G2 & G6

(19E501107, Rev. 13)



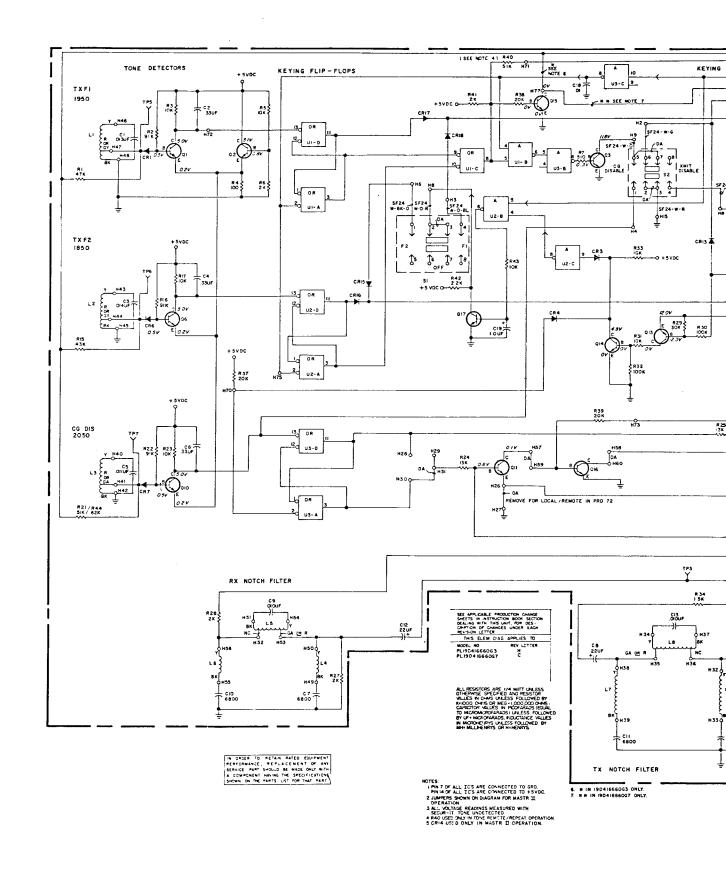
HEOWN ON DIAGRAM FOR MASTR II

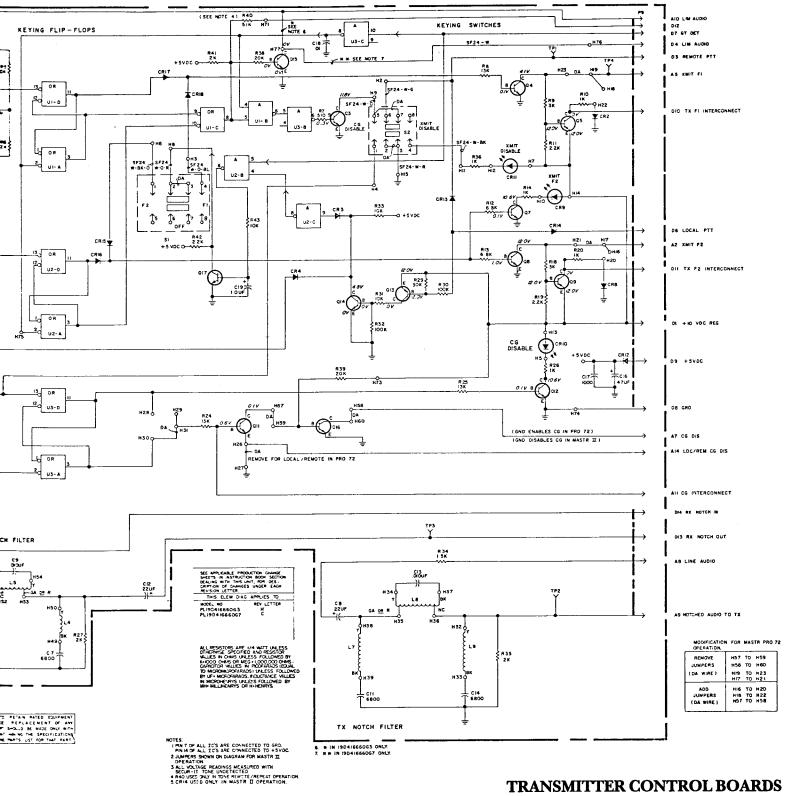
MEE READINGS MEASURED WITH SECUR-IT
TITECTED.

GELY IN TONE REMOTE/REPEAT OPERATION.

9 OBLY IN MASTR II OPERATION.

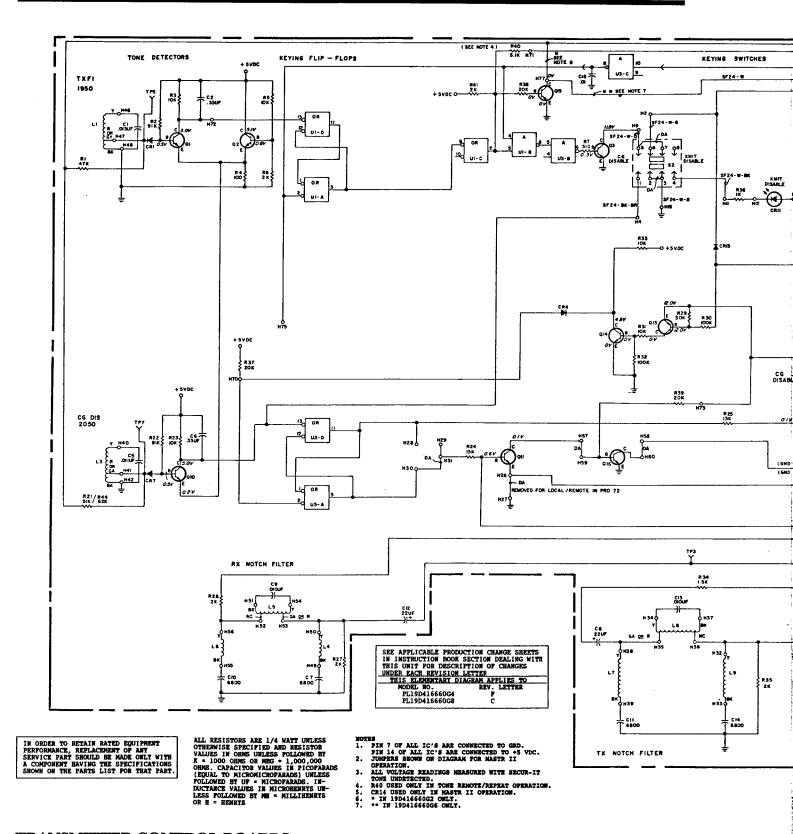
M1666002 ONLY.





19D416660G3 & G7

(19E501112, Rev. 16)



# TRANSMITTER CONTROL BOARDS

19D416660G4 & G8

(19E501106, Rev. 15)

